

MODULATOR

# MX-LN series

## 1550 nm band intensity Modulators

The MX-LN series are lithium niobate ( $\text{LiNbO}_3$ ) intensity modulators designed for optical communications at data rates up to 56 Gb/s.

The X-cut design of these Mach-Zehnder modulators confer them an unmatched stability in a wide range of operational conditions, as well as a zero chirp performance. Exail proprietary waveguide design offers a low insertion loss combined with a high contrast. The MX-LN series are ideally suited for few kb/s up to 56 Gb/s optical transmission with NRZ, RZ, DPSK, Duo Binary modulation formats and are key device for a large variety of high bandwidth applications.



### Features

- High bandwidth
- X-cut for high stability
- Low drive voltage
- Low insertion loss

### MX-LN-01 Performance Highlights\*

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	1550	1580	nm
Electro-optical bandwidth	100	400	-	GHz

### Applications

- Digital communications
- General purpose intensity modulation
- Test and measurement

### Options

- High extinction ratio versions
- 2000 nm, 1300 nm, 1060 nm, 850 nm
- Low insertion loss
- Space grade version

### Related Equipments

- RF amplifiers
- MBC-DG Automatic Bias Controllers
- Modbox-CBand-VNA

### MX-LN-05 Performance Highlights\*

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	1550	1580	nm
Electro-optical bandwidth	3	4	-	GHz

### MX-LN-10 Performance Highlights\*

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	1550	1625	nm
Electro-optical bandwidth	10	12	-	GHz

### MX-LN-20 Performance Highlights\*

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	1550	1625	nm
Electro-optical bandwidth	20	25	-	GHz

### MX-LN-40 Performance Highlights\*

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	1550	1625	nm
Electro-optical bandwidth	28	30	-	GHz

\*Specifications given at 25 °C, 1550 nm

**MX-LN-0.1**

## 100 MHz Intensity Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical bandwidth <sup>(i)</sup>	$S_{21}$	RF electrodes	100	400	-	MHz
Ripple $S_{21}^{(i)}$	$\Delta S_{21}$	RF electrodes	-	0.5	1	dB
Vπ RF @50 kHz	$V_{\pi_{RF \text{ 50 kHz}}}$	RF electrodes, @ 1550 nm	-	3.5	4	V
Vπ RF @200 Mb/s PRBS	$V_{\pi_{RF \text{ 200 Mb/s}}}$	RF electrodes, @ 1550 nm	-	1.5	-	V
Vπ DC electrodes	$V_{\pi_{DC}}$	DC electrodes	-	6.5	7	V
RF input impedance	$Z_{in-RF}$	From DC to 400 MHz	High impedance			
DC input impedance	$Z_{in-DC}$	-	1	-	-	MΩ

<sup>(i)</sup> DC coupled amplitude modulator. RF modulation applies from DC to 400 MHz

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	$\lambda$	-	1530	1550	1580	nm
Insertion loss	IL	Without optical connectors <sup>(ii)</sup>	-	3.5	4.5	dB
DC Extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	30	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	$\alpha$	-	-0.1	-	0.1	-

All specifications given at 25 °C, 1550 nm, unless differently specified.

<sup>(ii)</sup> Consider an extra-loss up to 0.25 dB for each FC/APC optical connector

**Absolute Maximum Ratings**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
RF input power	$EP_{in}$	-	N/A	-
Bias Voltage	$V_{bias}$	-20	+20	V
Optical input power	$OP_{in}$	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**MX-LN-05**

## 5 GHz Intensity Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical bandwidth	S <sub>21</sub>	RF electrodes	3	4	-	GHz
Ripple S <sub>21</sub>	ΔS <sub>21</sub>	RF electrodes	-	0.5	1	dB
Electrical return loss, 0-5 GHz	S <sub>11</sub>	RF electrodes	-	-13	-10	dB
Vπ RF @50 kHz	Vπ <sub>RF 50 kHz</sub>	RF electrodes, @ 1550 nm	-	3.5	4	V
Vπ DC electrodes	Vπ <sub>DC</sub>	DC electrodes	-	6.5	7	V
RF input impedance	Z <sub>in-RF</sub>	-	-	50	-	Ω
DC input impedance	Z <sub>in-DC</sub>	-	1	-	-	MΩ

50 Ω RF input

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Operating wavelength	λ	-	1530	1550	1580	nm
Insertion loss	IL	Without optical connectors <sup>(i)</sup>	-	3.5	4.5	dB
DC Extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	25	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	-	0.1	-

All specifications given at 25 °C, 1550 nm, unless differently specified.

<sup>(i)</sup> Consider an extra-loss up to 0.25 dB for each FC/APC optical connector**Absolute Maximum Ratings**

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Parameter	Symbol	Min	Max	Unit
RF input power	EP <sub>in</sub>	-	28	dBm
Bias Voltage	V <sub>bias</sub>	-20	+20	V
Optical input power	OP <sub>in</sub>	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**MX-LN-10**

## 10 GHz Intensity Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical bandwidth	$S_{21}$	RF electrodes	10	12	-	GHz
Ripple $S_{21}$	$\Delta S_{21}$	RF electrodes	-	0.5	1	dB
Electrical return loss	$S_{11}$	RF electrodes	-	-12	-10	dB
Vπ RF @50 kHz	$V\pi_{RF \text{ 50 kHz}}$	RF electrodes, @ 1550 nm	-	5.5	6.5	V
Vπ RF @10 Gb/s PRBS	$V\pi_{RF \text{ 10 Gb/s}}$	RF electrodes, @ 1550 nm	-	6.5	7	V
Vπ DC electrodes	$V\pi_{DC}$	DC electrodes	-	6.5	7	V
RF input impedance	$Z_{in-RF}$	-	-	50	-	$\Omega$
DC input impedance	$Z_{in-DC}$	-	-	1	-	$M\Omega$
50 $\Omega$ RF input						

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Operating wavelength	$\lambda$	-	1530	1550	1625	nm
Insertion loss	IL	Without optical connectors <sup>(i)</sup>	-	3.5	-	dB
Insertion loss (with low IL option)	LIL	Without optical connector <sup>(i)</sup>	-	2.7	3	dB
DC Extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	$\alpha$	-	-0.1	0	0.1	-

All specifications given at 25 °C, 1550 nm, unless differently specified.

<sup>(i)</sup> Consider an extra-loss up to 0.25 dB for each FC/APC optical connector**Absolute Maximum Ratings**

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Parameter	Symbol	Min	Max	Unit
RF input power	$EP_{in}$	-	28	
Bias Voltage	$V_{bias}$	-20	+20	V
Optical input power	$OP_{in}$	-	20	dBm
Operating temperature	OT	0	+70	°C

**MX-LN-20**

## 20 GHz Intensity Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical bandwidth	$S_{21}$	RF electrodes, from 2 GHz	20	25	-	GHz
Ripple $S_{21}$	$\Delta S_{21}$	RF electrodes, $f < 20$ GHz	-	0.5	1	dB
Electrical return loss	$S_{11}$	RF electrodes	-	-12	-10	dB
V $\pi$ RF @50 kHz	$V\pi_{RF \text{ 50 kHz}}$	RF electrodes, @ 1550 nm	-	5	5.5	V
V $\pi$ RF @20 Gb/s PRBS	$V\pi_{RF \text{ 20 Gb/s}}$	RF electrodes, @ 1550 nm	-	5.5	6	V
V $\pi$ DC electrodes	$V\pi_{DC}$	DC electrodes	-	6.5	7	V
RF input impedance	$Z_{in-RF}$	-	-	50	-	$\Omega$
DC input impedance	$Z_{in-DC}$	-	-	1	-	$M\Omega$

50  $\Omega$  RF input**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Operating wavelength	$\lambda$	-	1530	1550	1625	nm
Insertion loss	IL	Without connector <sup>(1)</sup>	-	3.5	4.5	dB
DC Extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	$\alpha$	-	-0.1	0	0.1	-

All specifications given at 25 °C, 1550 nm, unless differently specified.

<sup>(1)</sup> Consider an extra-loss up to 0.25 dB for each FC/APC optical connector**Absolute Maximum Ratings**

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Parameter	Symbol	Min	Max	Unit
RF input power	$EP_{in}$	-	28	dBm
Bias Voltage	$V_{bias}$	-20	+20	V
Optical input power	$OP_{in}$	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**MX-LN-40**

## 40 GHz Intensity Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical bandwidth	$S_{21}$	RF electrodes, from 2 GHz	28	30	-	GHz
Ripple $S_{21}$	$\Delta S_{21}$	RF electrodes, $f < 30$ GHz	-	0.5	1	dB
Electrical return loss	$S_{11}$	RF electrodes	-	-12	-10	dB
V $\pi$ RF @50 kHz	$V\pi_{RF \text{ 50 kHz}}$	RF electrodes, @ 1550 nm	-	5	6	V
V $\pi$ DC electrodes	$V\pi_{DC}$	DC electrodes, @ 1550 nm	-	6.5	7	V
RF input impedance	$Z_{in-RF}$	-	-	50	-	$\Omega$
DC input impedance	$Z_{in-DC}$	-	1	-	-	$M\Omega$

50  $\Omega$  RF input**Optical Characteristics**

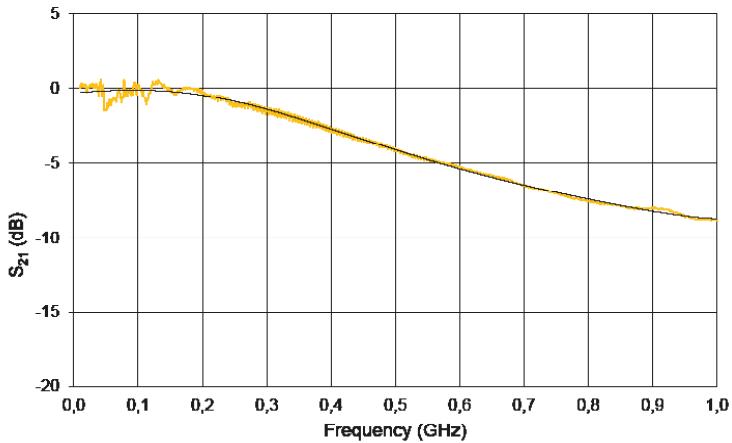
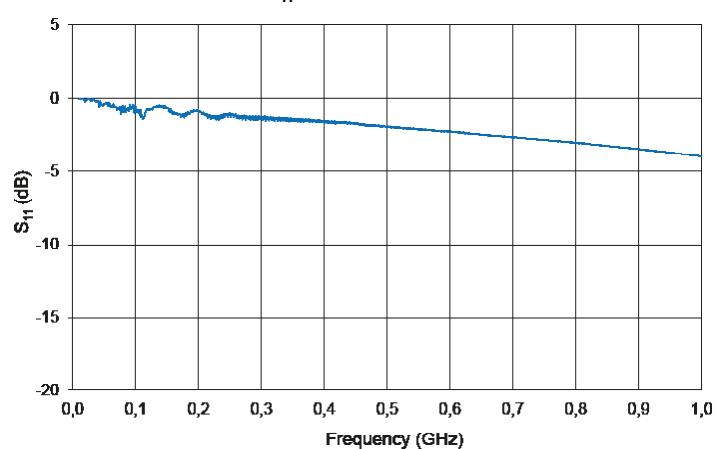
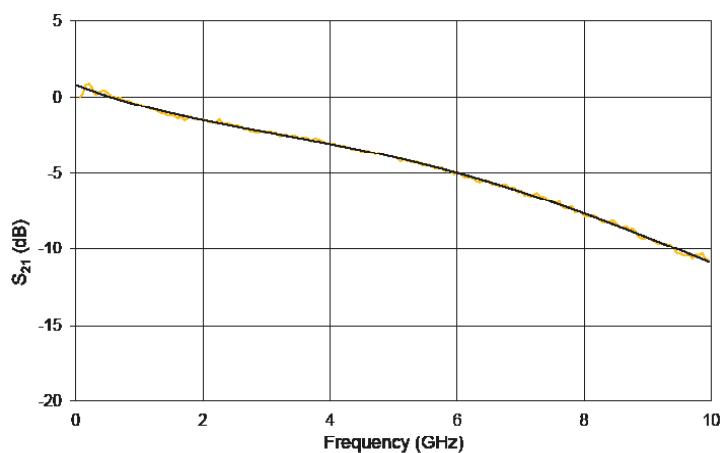
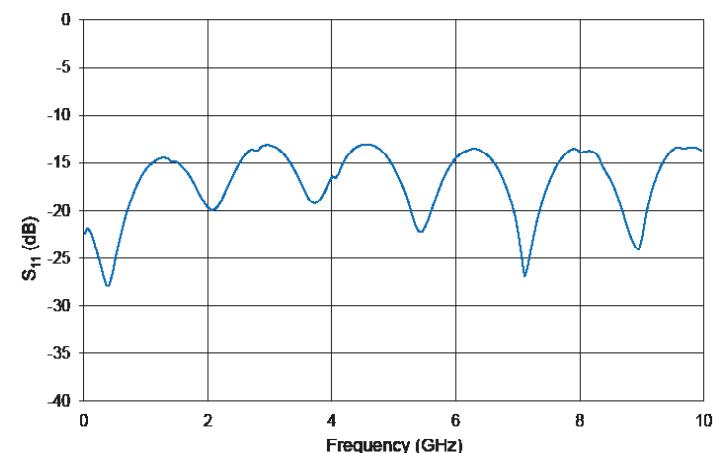
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Operating wavelength	$\lambda$	-	1530	1550	1625	nm
Insertion loss	IL	Without optical connectors <sup>(i)</sup>	-	3.5	4.5	dB
DC Extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	$\alpha$	-	-0.1	0	0.1	-

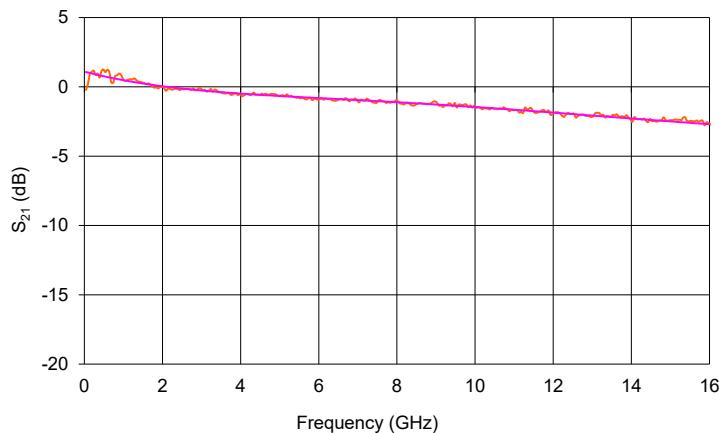
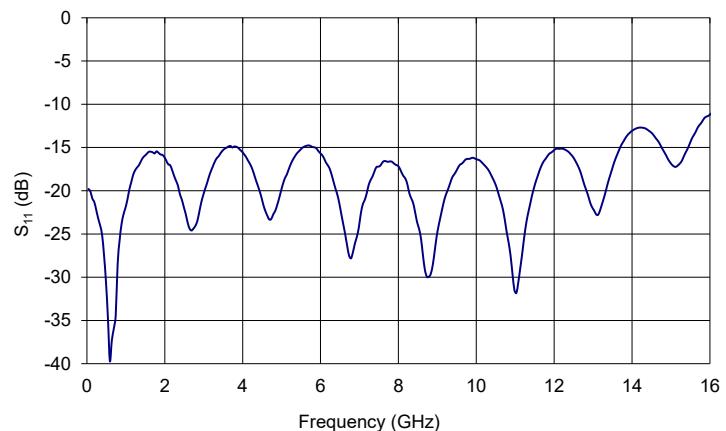
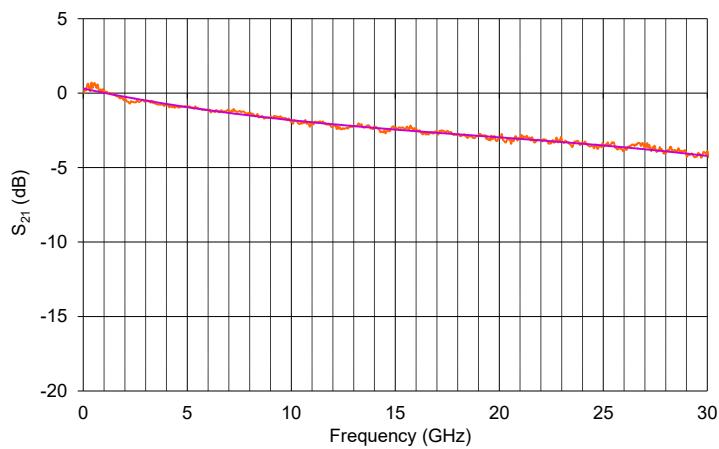
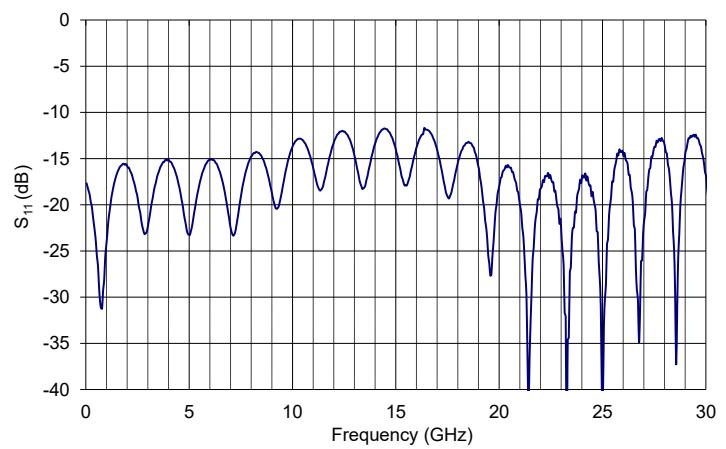
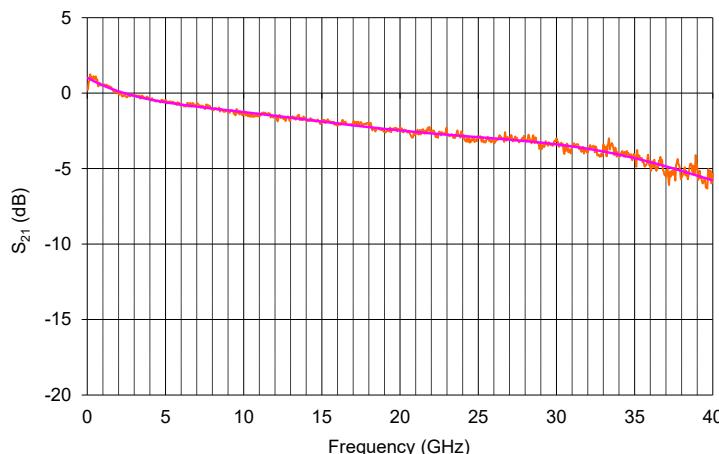
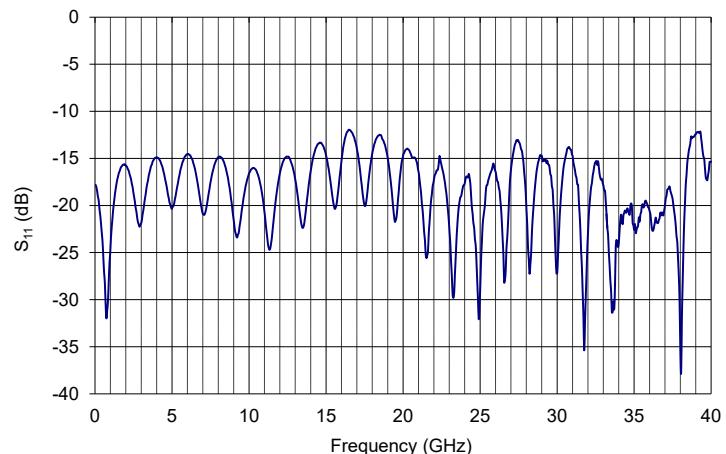
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<sup>(i)</sup> Consider an extra-loss up to 0.25 dB for each FC/APC optical connector**Absolute Maximum Ratings**

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Bias Voltage	$V_{bias}$	-20	+20	V
Optical input power	$OP_{in}$	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

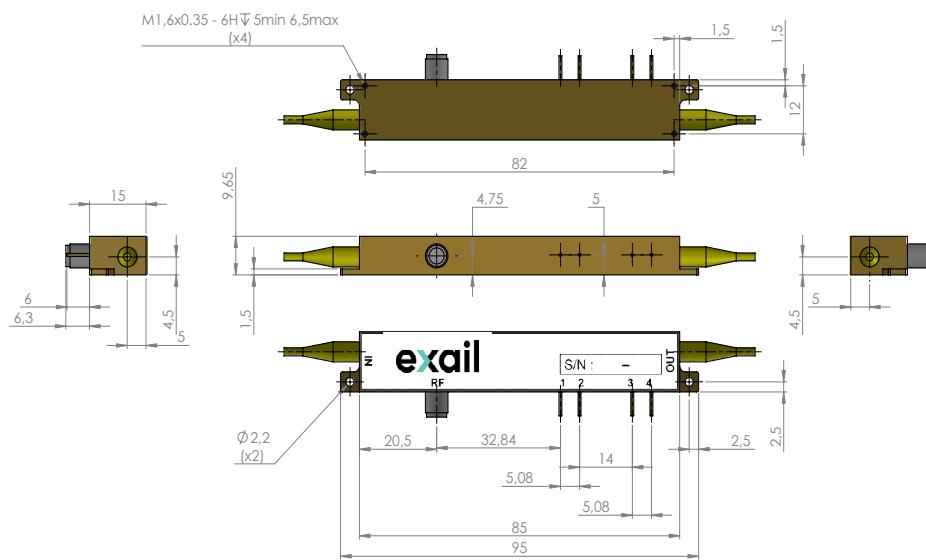
**MX-LN-0.1 & 05**MX-LN-0.1 Typical  $S_{21}$  CurveMX-LN-0.1 Typical  $S_{11}$  CurveMX-LN-05 Typical  $S_{21}$  CurveMX-LN-05 Typical  $S_{11}$  Curve

**MX-LN-10, 20 & 40****MX-LN-10 Typical S<sub>21</sub> Curve****MX-LN-10 Typical S<sub>11</sub> Curve****MX-LN-20 Typical S<sub>21</sub> Curve****MX-LN-20 Typical S<sub>11</sub> Curve****MX-LN-40 Typical S<sub>21</sub> Curve****MX-LN-40 Typical S<sub>11</sub> Curve**

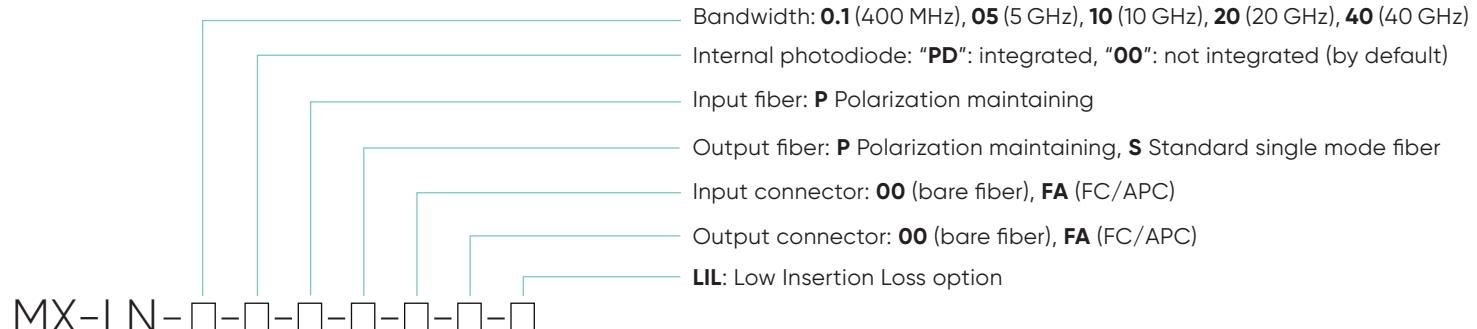
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## Mechanical Diagram and Pinout

All measurements in mm



## Ordering information



## About us

Exail reserves the right to change, at any time and without notice, the specifications, design, function or form of its products described herein.

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